forming a third insulating layer over the second insulating layer and pattern of second metallic elements; and

forming a planar capacitor comprising two enmeshed comb shaped electrodes on the third insulating layer.

**12**. The method of claim **11** wherein the first metallic segments formed on the first insulating layer include a segment having a temperature dependent electrical resistance located only over the peripheral portion of the substrate.

**13**. The method of claim **12** including the further step of providing holes through the first, second and third insulating layers in the central region of the substrate.

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